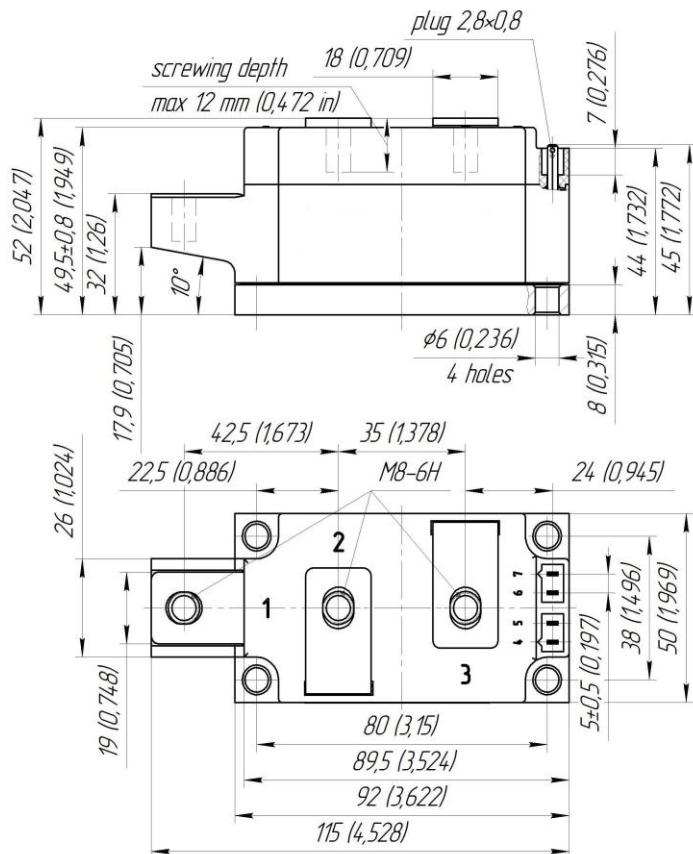
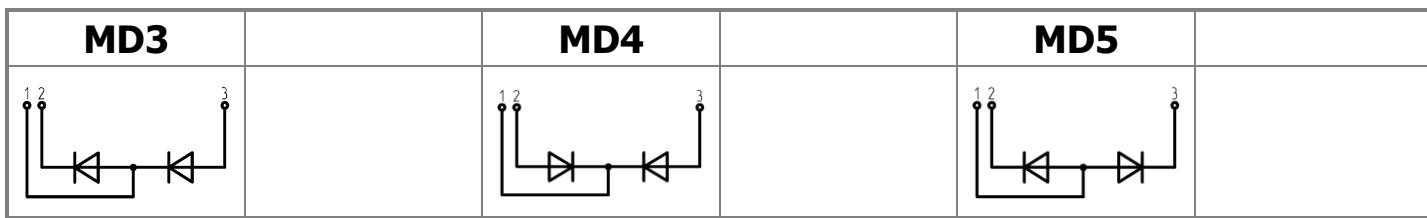




Electrically isolated base plate
Industrial standard package
Simplified mechanical design, rapid assembly
Pressure contact

**Double Diode Module
For Phase Control
MDx-400-18-C1**

Average forward current	I _{FAV}	400 A
Repetitive peak reverse voltage	V _{RRM}	1000 ÷ 1800 V
V _{RRM} , V	1000	1200
Voltage code	10	12
T _j , °C	14	16
	18	- 40 ÷ 150



All dimensions in millimeters (inches)

MAXIMUM ALLOWABLE RATINGS

Symbols and parameters		Units	Values	Test conditions	
ON-STATE					
I _{FAV}	Average forward current	A	400 445	T _c = 106 °C; T _c = 100 °C; 180° half-sine wave; 50 Hz	
I _{FRMS}	RMS forward current	A	628	T _c = 106 °C; 180° half-sine wave; 50 Hz	
I _{FSM}	Surge forward current	kA	12.0 14.0	T _j =T _j max T _j =25 °C	180° half-sine wave; 50 Hz (t _p =10 ms); single pulse; V _R =0 V;
			13.0 15.0	T _j =T _j max T _j =25 °C	180° half-sine wave; 60 Hz (t _p =8.3 ms); single pulse; V _R =0 V;
I ² t	Safety factor	A ² s·10 ³	720 980	T _j =T _j max T _j =25 °C	180° half-sine wave; 50 Hz (t _p =10 ms); single pulse; V _R =0 V;
			700 930	T _j =T _j max T _j =25 °C	180° half-sine wave; 60 Hz (t _p =8.3 ms); single pulse; V _R =0 V;

BLOCKING

V _{RRM}	Repetitive peak reverse voltages	V	1000÷1800	T _{j min} < T _j <T _{j max} ; 180° half-sine wave; 50 Hz;
V _{RSM}	Non-repetitive peak reverse voltages	V	1100÷1900	T _{j min} < T _j <T _{j max} ; 180° half-sine wave; 50 Hz; single pulse;
V _R	Reverse continuous voltages	V	0.75·V _{RRM}	T _j =T _j max;

THERMAL

T _{stg}	Storage temperature	°C	- 40 ÷ 125	
T _j	Operating junction temperature	°C	- 40 ÷ 150	

MECHANICAL

a	Acceleration under vibration	m/s ²	50	
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CHARACTERISTICS

Symbols and parameters		Units	Values	Conditions
ON-STATE				
V _{FM}	Peak forward voltage, max	V	1.20	T _j =25 °C; I _{FM} =785 A
V _{F(TO)}	Forward threshold voltage, max	V	0.75	T _j =T _j max;
r _T	Forward slope resistance, max	mΩ	0.250	0.5 π I _{FAV} < I _T < 1.5 π I _{FAV}
BLOCKING				
I _{RRM}	Repetitive peak reverse current, max	mA	30	T _j =T _j max; V _R =V _{RRM}
SWITCHING				
Q _{rr}	Total recovered charge, max	µC	1200	T _j =T _j max; I _{TM} =400 A; di _R /dt=-10 A/µs; V _R =100 V
t _{rr}	Reverse recovery time, max	µs	20	
I _{rrM}	Peak reverse recovery current, typ	A	120	
THERMAL				
R _{thjc}	Thermal resistance, junction to case			180° half-sine wave, 50 Hz
	per module	°C/W	0.0550	
	per arm	°C/W	0.1100	
R _{thch}	Thermal resistance, case to heatsink			
	per module	°C/W	0.0200	
	per arm	°C/W	0.0400	

INSULATION						
V _{ISOL}	Insulation test voltage	kV	3.00	Sine wave, 50 Hz;	t=1 min	
			3.60	RMS	t=1 sec	
MECHANICAL						
M ₁	Mounting torque (M5) ¹⁾		Nm	6.00	Tolerance ± 15%	
M ₂	Terminal connection torque (M8) ¹⁾		Nm	9.00	Tolerance ± 15%	
w	Weight		g	800		

PART NUMBERING GUIDE						NOTES
MD 3 - 400 - 18 - C1 - N						¹⁾ The screws must be lubricated
1	2	3	4	5	6	

1. MD - Rectifier Diode
 2. Circuit Schematic
 3. Average Forward Current, A
 4. Voltage Code
 5. Package Type (M.C1)
 6. Ambient Conditions:
 N – Normal

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 In the interest of product improvement, Proton-Electrotex reserves the right to change data sheet without notice.

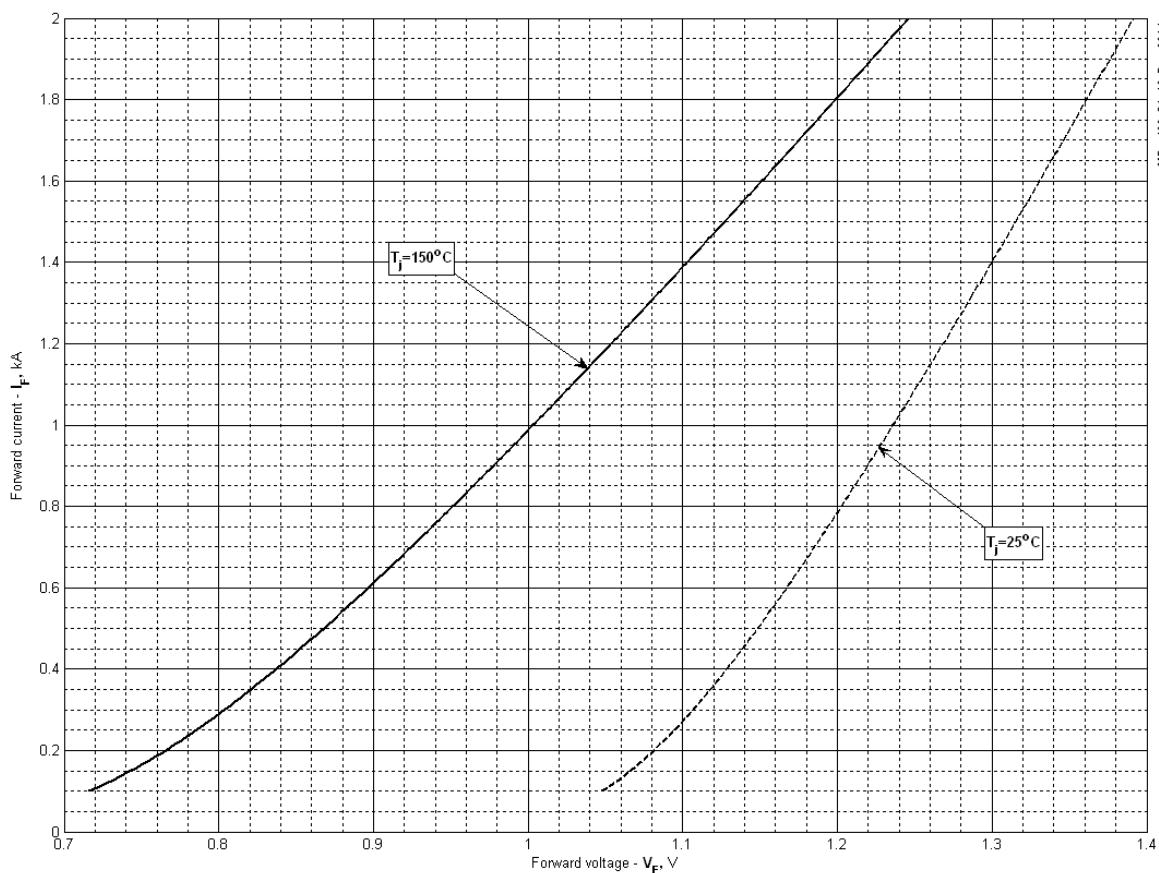


Fig 1 – On-state characteristics of Limit device

Analytical function for On-state characteristic:

$$V_T = A + B \cdot i_T + C \cdot \ln(i_T + 1) + D \cdot \sqrt{i_T}$$

	Coefficients for max curves	
	$T_j = 25^\circ\text{C}$	$T_j = T_{j\max}$
A	0.966957	0.599043
B	0.106743	0.173890
C	-0.157781	-0.223965
D	0.271640	0.385583

On-state characteristic model (see Fig. 1)

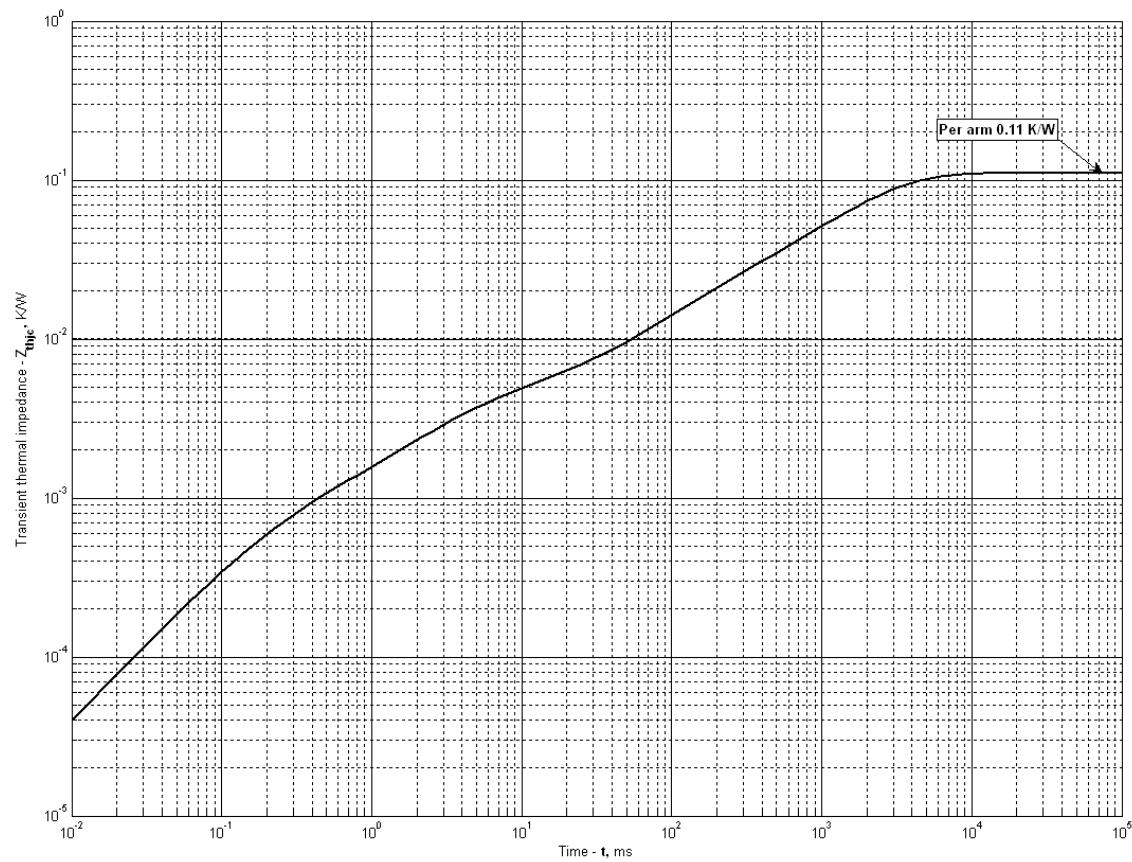


Fig 2 – Transient thermal impedance

Analytical function for Transient thermal impedance junction to case Z_{thjc} for DC:

$$Z_{thjc} = \sum_{i=1}^n R_i \left(1 - e^{-\frac{t}{\tau_i}} \right)$$

Where $i = 1$ to n , n is the number of terms in the series.

t = Duration of heating pulse in seconds.

Z_{thjc} = Thermal resistance at time t.

R_i = Amplitude of p_{th} term.

τ_i = Time constant of r_{th} term.

i	1	2	3	4	5	6
R_i , K/W	0.1293	0.01314	0.02771	-0.05535	0.0528	0.002749
τ_i , s	2.823	1.393	0.3322	0.0611	0.05731	0.002173

Transient thermal impedance junction to case Z_{thjc} model (see Fig. 2)

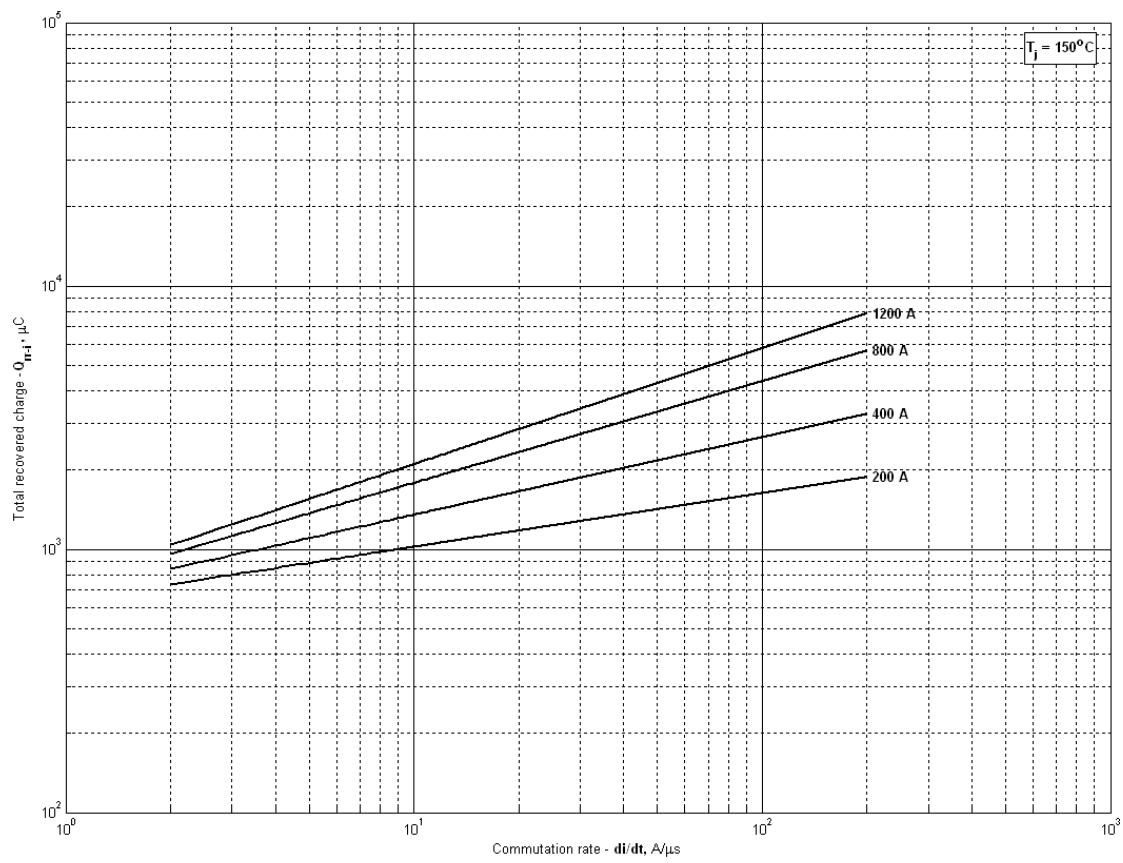


Fig 3 - Total recovered charge, Q_{rr-i} (integral)

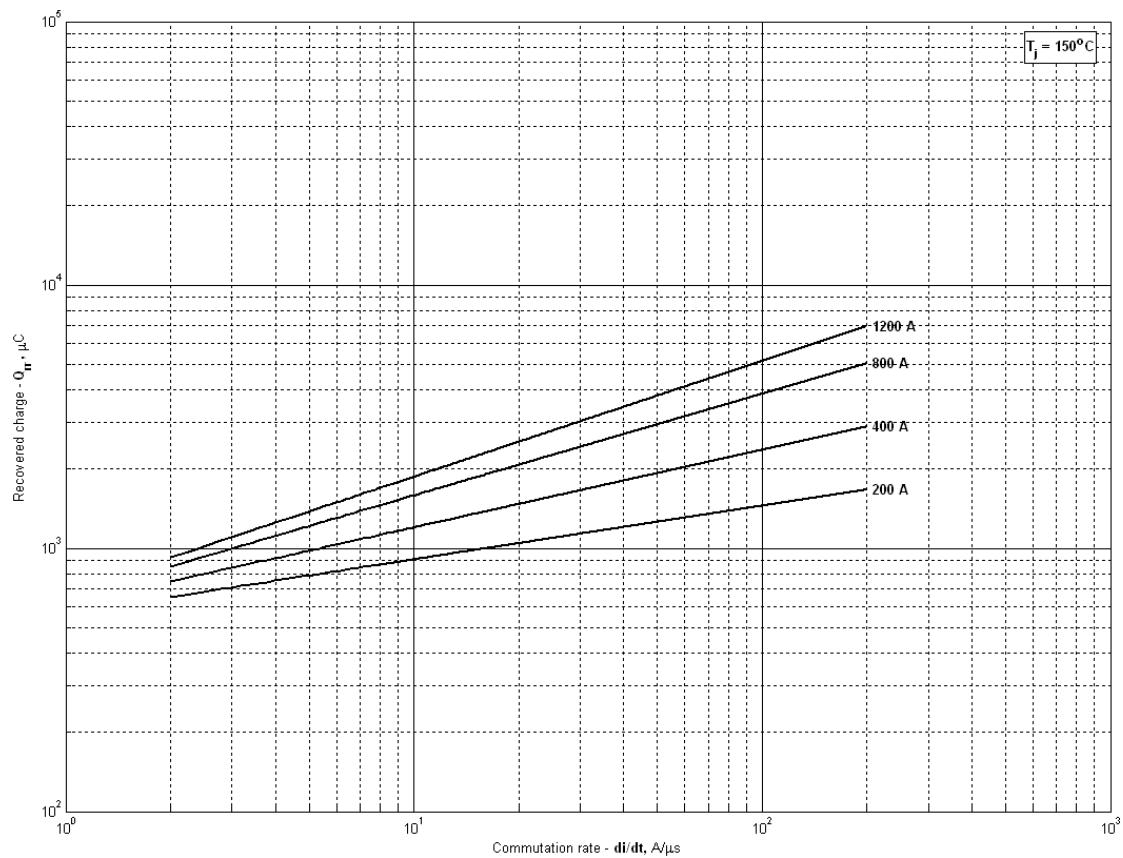


Fig 4 - Recovered charge, Q_{rr} (linear)

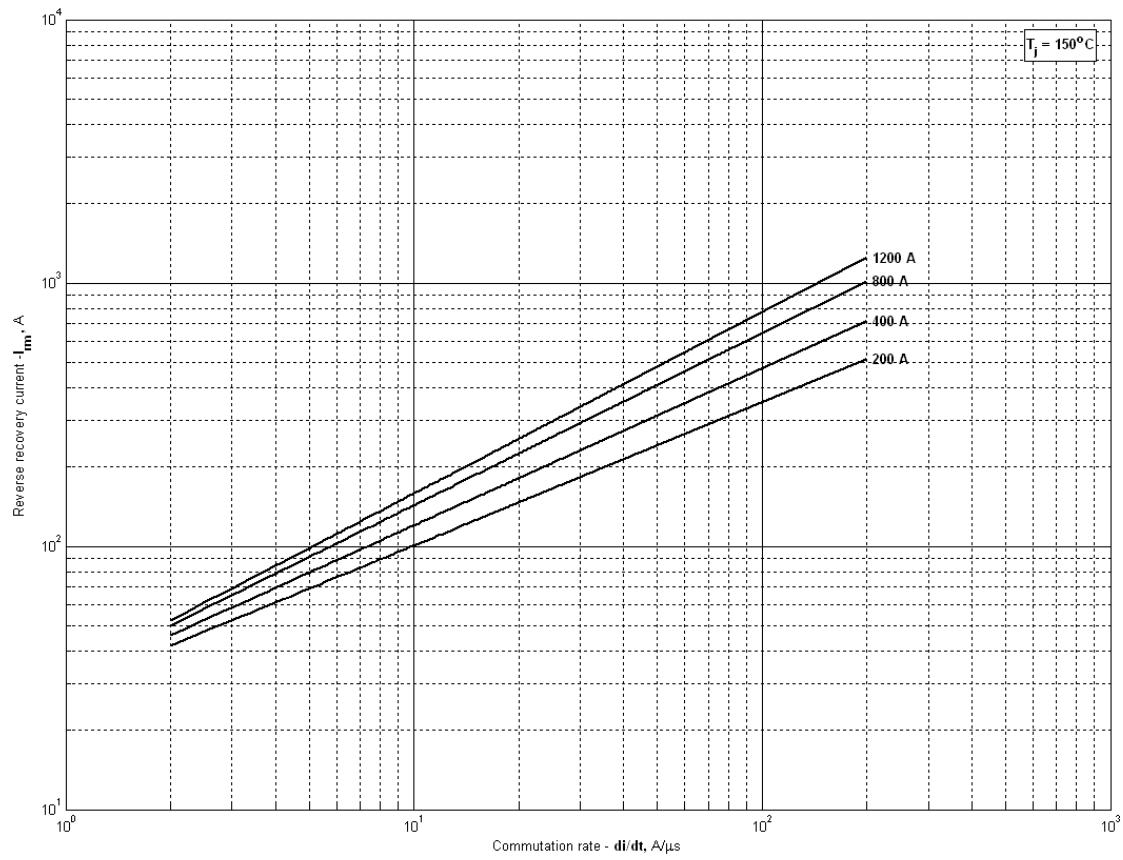


Fig 5 - Peak reverse recovery current, I_{rm}

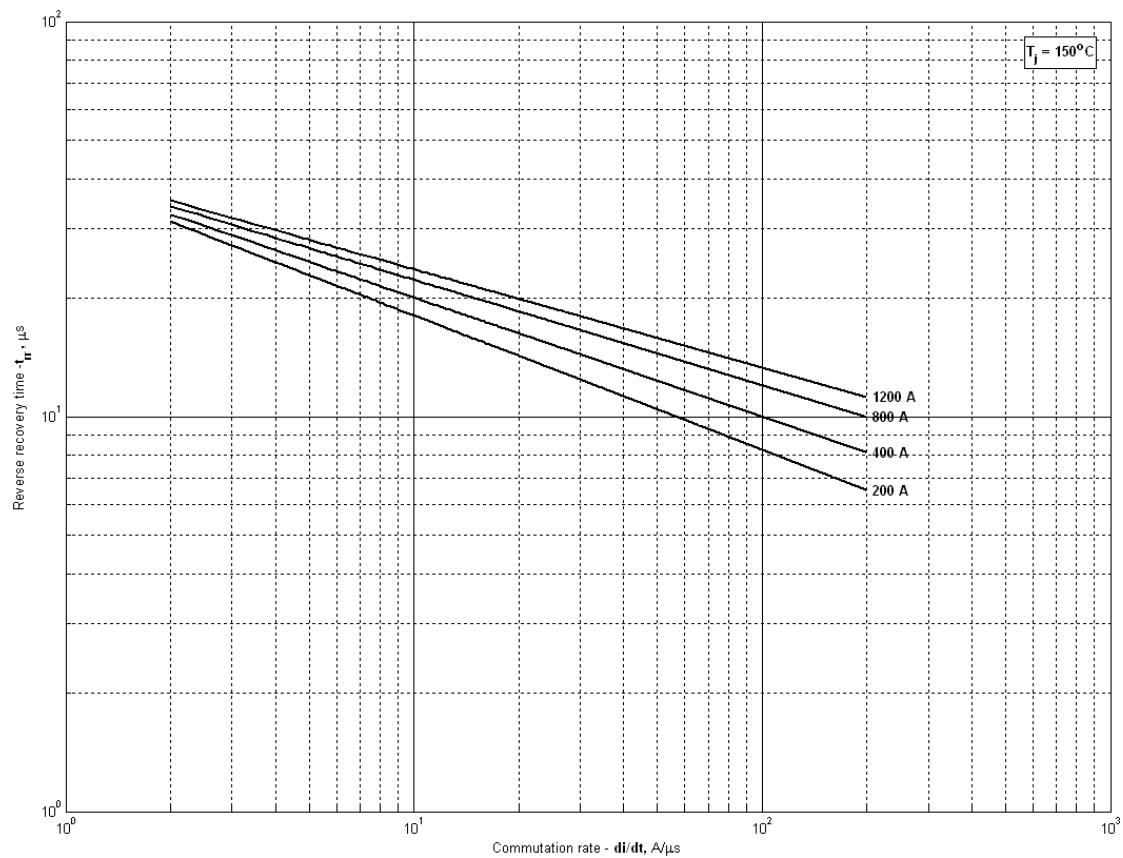


Fig 6 - Recovery time, t_{rr} (50% chord)

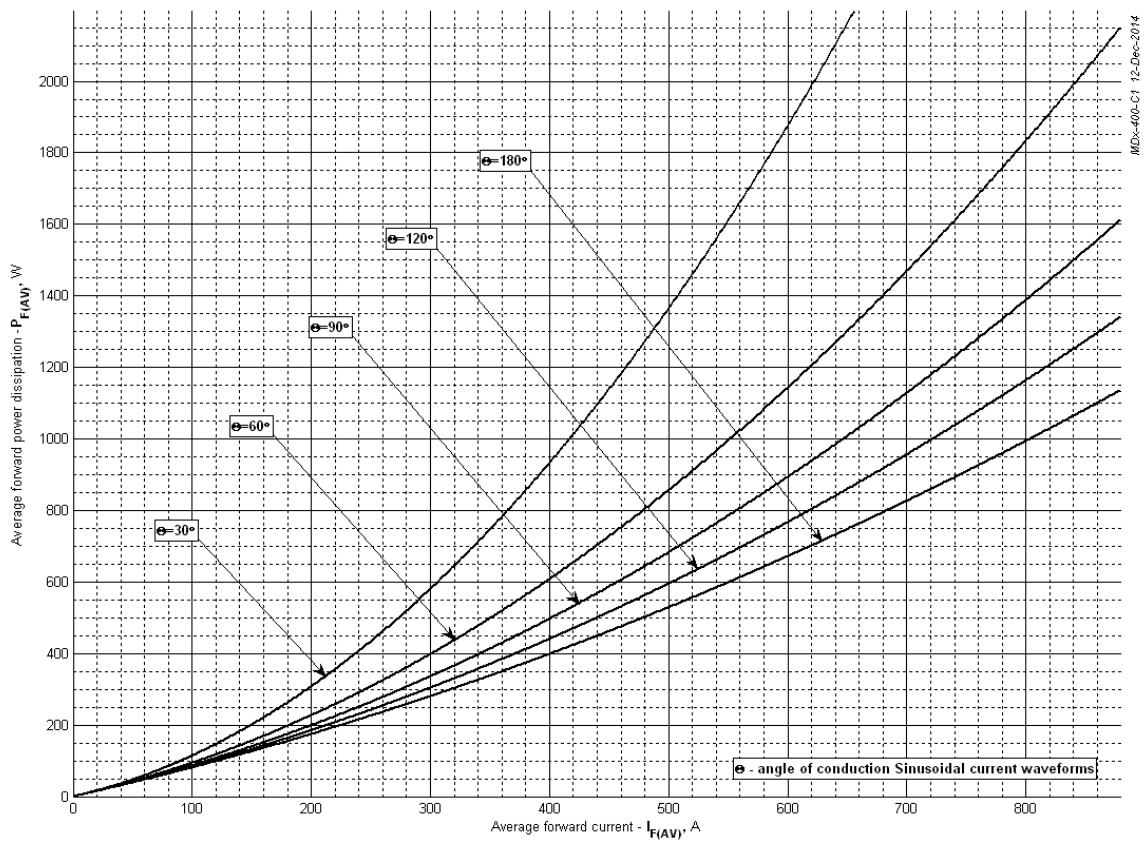


Fig 7 – On-state power loss (sinusoidal current waveforms)

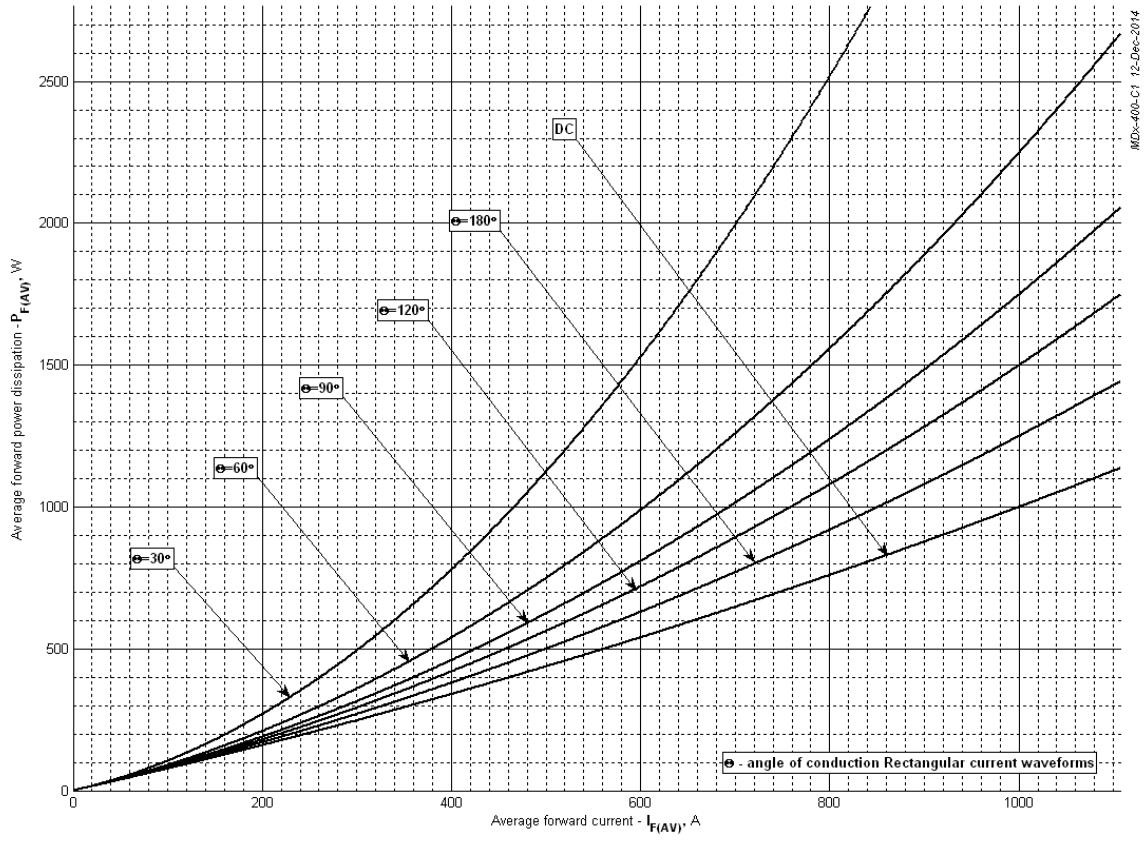


Fig 8 - On-state power loss (rectangular current waveforms)

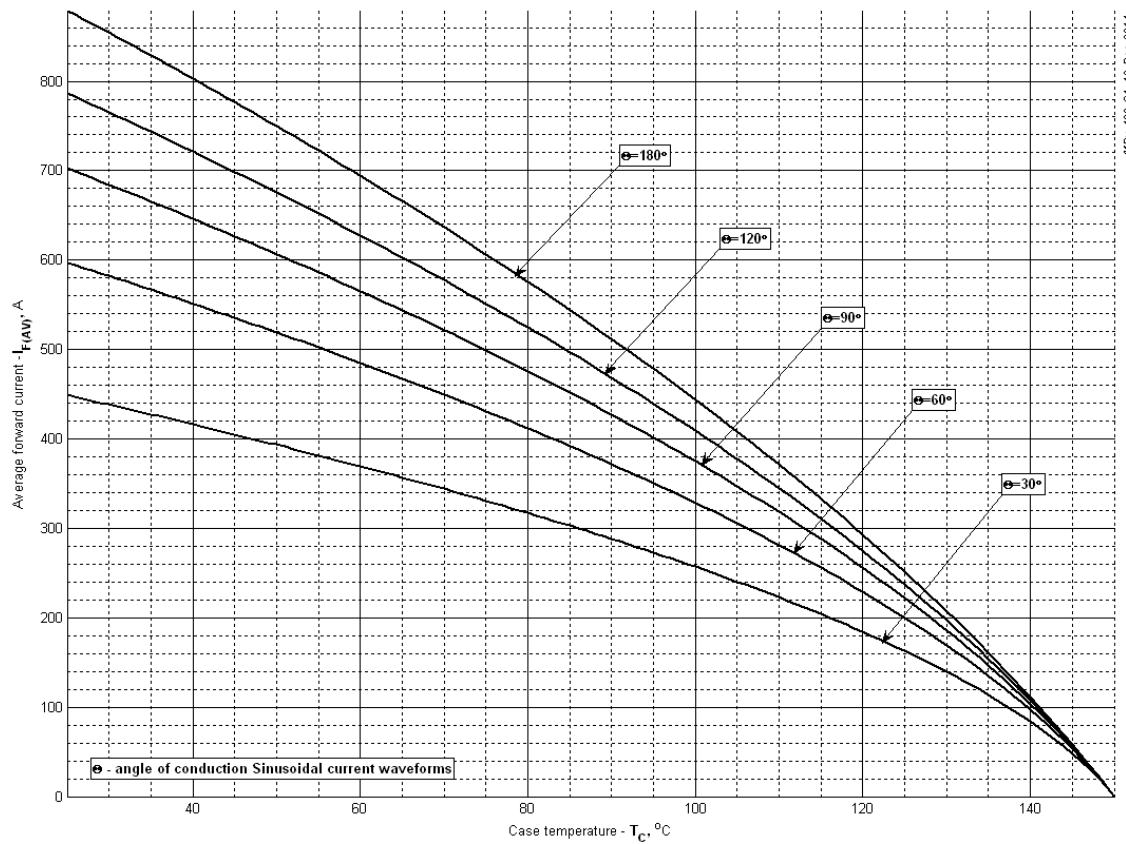


Fig 9 – Maximum case temperature (sinusoidal current waveforms)

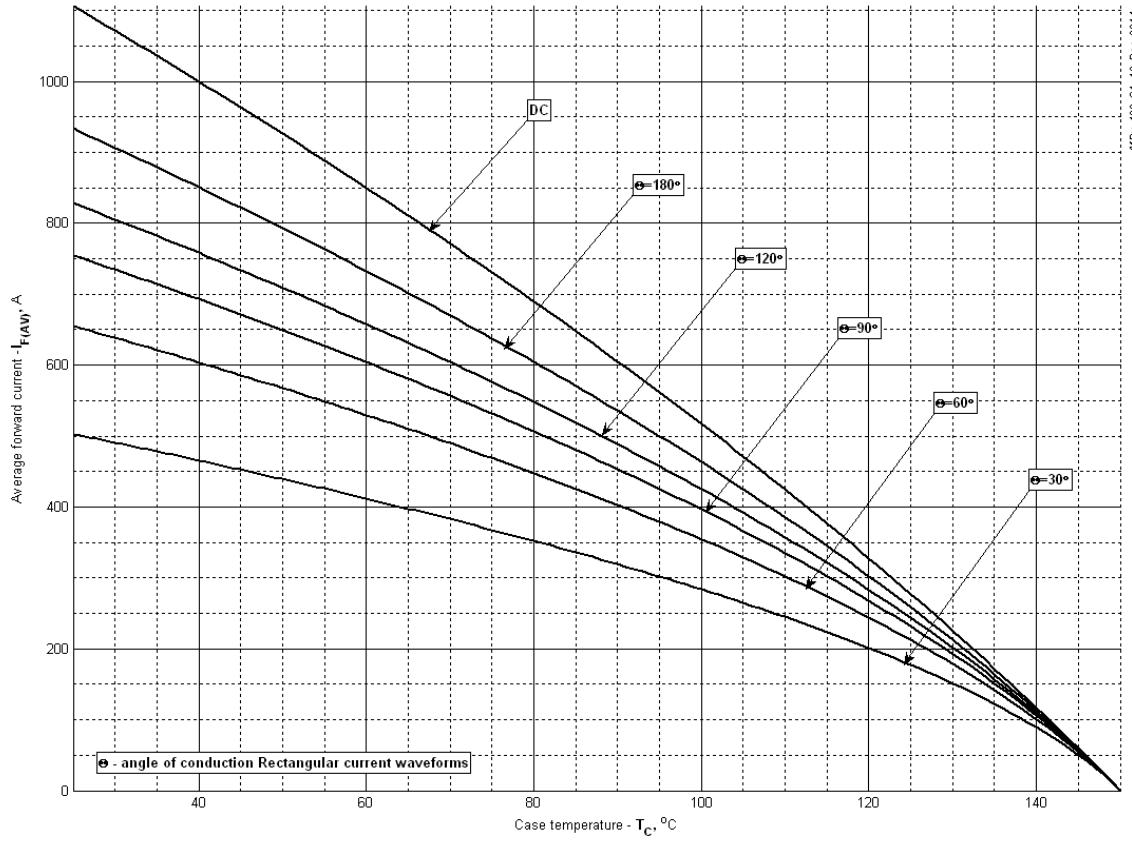


Fig 10 - Maximum case temperature (rectangular current waveforms)

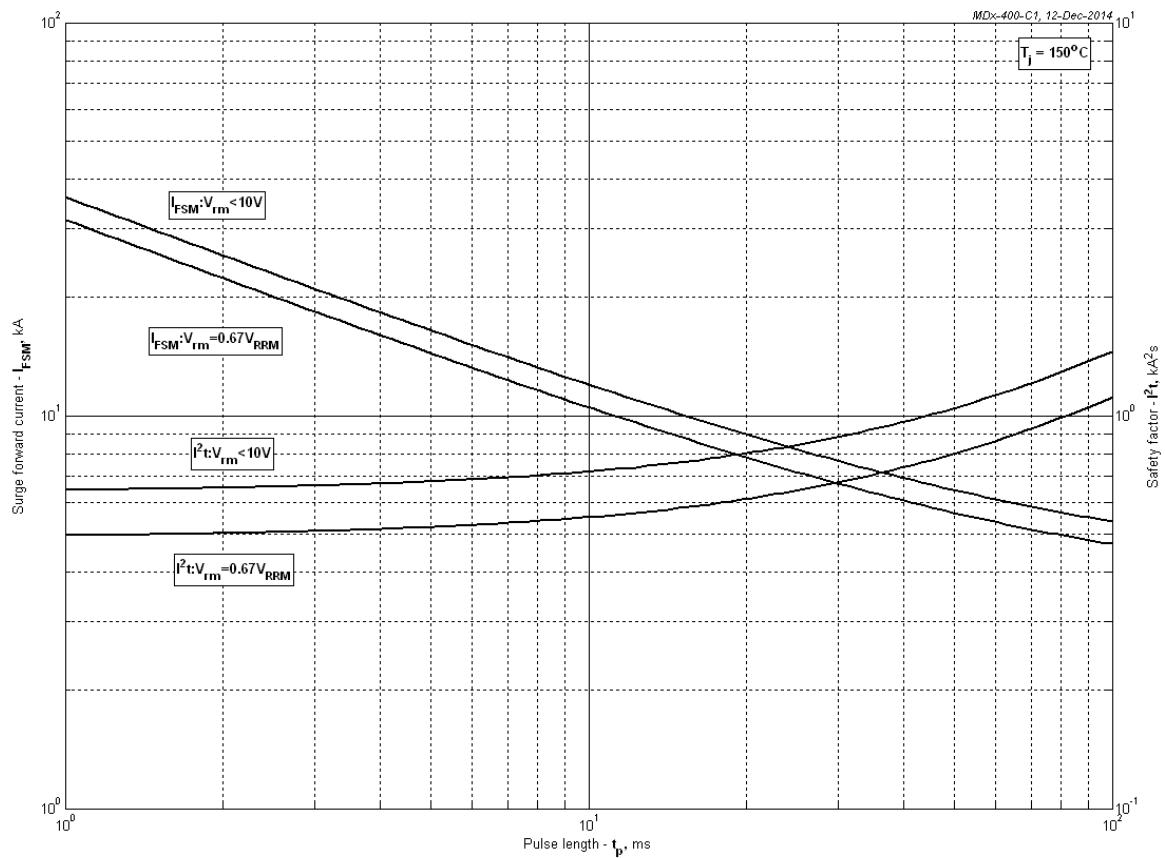


Fig 11 – Maximum surge and I^2t ratings

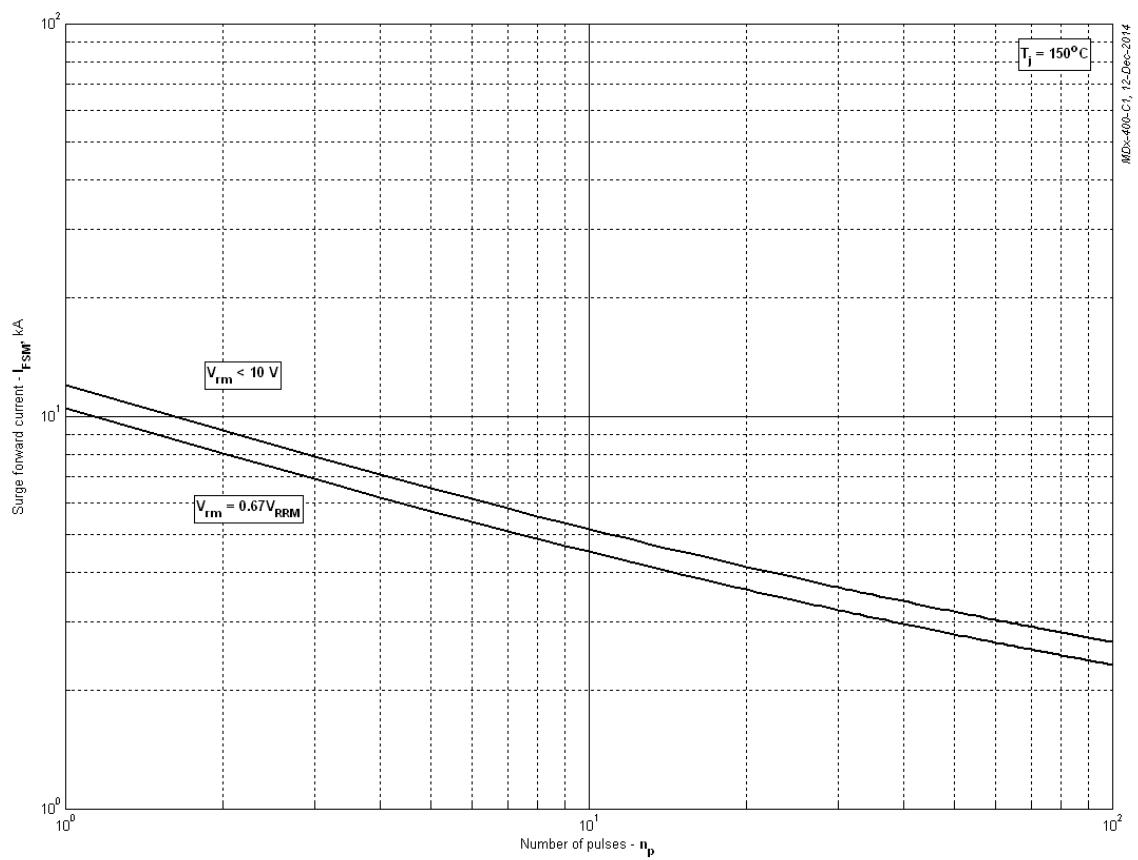


Fig 12 - Maximum surge ratings